

# WS1111

## 4 x 4 Power Amplifier Module for CDMA/AMPS (824 – 849 MHz)

### Data Sheet

#### Description

The WS1111 is a CDMA (Code Division Multiple Access) and AMPS (advance mobile phone service) Power Amplifier (PA), designed for handsets operating in the 824~849 MHz bandwidth.

The WS1111 features CoolPAM circuit technology that offers state-of-the-art reliability, temperature stability and ruggedness.

Digital mode control of CoolPAM reduces current consumption, which enables extended talk time of mobile devices.

The WS1111 meets stringent CDMA linearity requirements to and beyond 28 dBm output power. The 4 mm x 4 mm form factor 10-pin surface mount package is self contained, incorporating 50ohm input and output matching networks.

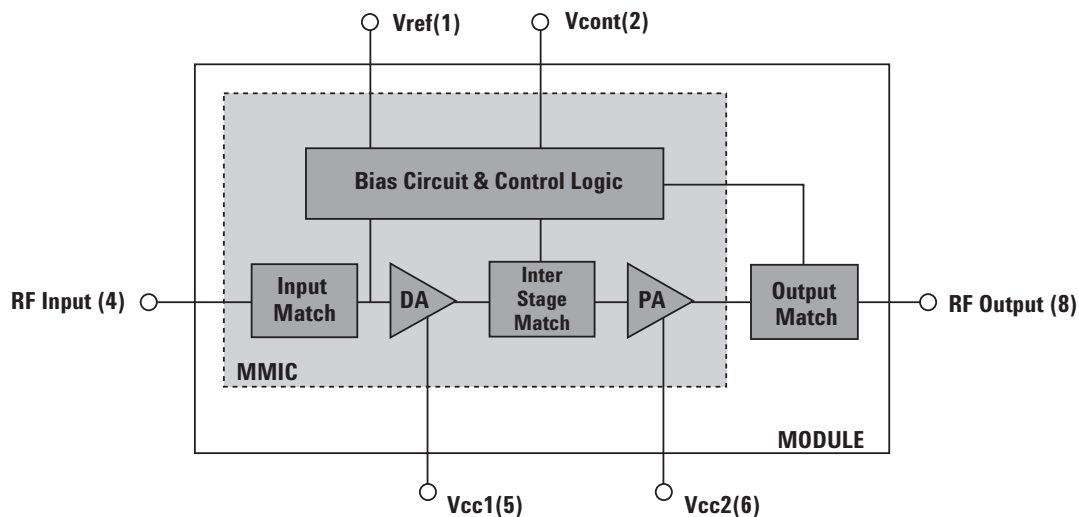
#### Features

- Good linearity
- High efficiency:  
41% at Pout = 28 dBm  
18% at Pout = 16 dBm
- 10-pin surface mounting package  
(4 mm x 4 mm x 1.4 mm)
- Internal 50Ω matching networks for both RF input and output
- CDMA 95A/B, CDMA2000-1X/EVDO

#### Applications

- Digital Cellular (CDMA)
- Analog Cellular (AMPS)

#### Functional Block Diagram



#### Ordering Information

| Part Number | No. of Devices | Container         |
|-------------|----------------|-------------------|
| WS1111      | 2500           | 13" Tape and Reel |

**Table 1. Absolute Maximum Ratings<sup>[1]</sup>**

| Parameter            | Symbol     | Min. | Nominal | Max. | Unit |
|----------------------|------------|------|---------|------|------|
| RF Input Power       | $P_{in}$   | –    | –       | 10.0 | dBm  |
| DC Supply Voltage    | $V_{cc}$   | –    | 3.4     | 6.0  | V    |
| DC Reference Voltage | $V_{ref}$  | –    | 2.85    | 3.3  | V    |
| DC Control Voltage   | $V_{cont}$ | –    | 2.85    | 3.3  | V    |
| Storage Temperature  | $T_{stg}$  | -55  | –       | +125 | °C   |

**Table 2. Recommended Operating Conditions**

| Parameter                  | Symbol     | Min. | Nominal | Max. | Unit |
|----------------------------|------------|------|---------|------|------|
| DC Supply Voltage          | $V_{cc}$   | 3.2  | 3.4     | 4.2  | V    |
| DC Reference Voltage       | $V_{ref}$  | 2.80 | 2.85    | 2.90 | V    |
| Mode Control Voltage       |            |      |         |      |      |
| – High Bias Mode           | $V_{cont}$ | –    | 0       | –    | V    |
| – Low Bias Mode            | $V_{cont}$ | –    | 2.85    | –    | V    |
| Operating Frequency        | $F_o$      | 824  | –       | 849  | MHz  |
| Case Operating Temperature | $T_o$      | -30  | 25      | 85   | °C   |

**Table 3. Power Range Truth Table**

| Power Mode      | Symbol | Vref | Vcont <sup>[2]</sup> | Range   |
|-----------------|--------|------|----------------------|---------|
| High Power Mode | PR2    | 2.85 | Low                  | ~28 dBm |
| Low Power Mode  | PR1    | 2.85 | High                 | ~16 dBm |
| Shut Down Mode  | –      | 0.00 | Low                  | –       |

**Notes:**

1. No damage assuming only one parameter is set at limit at a time with all other parameters set at or below nominal value.
2. High (2.0V – 3.0V), Low (0.0V – 0.5V).

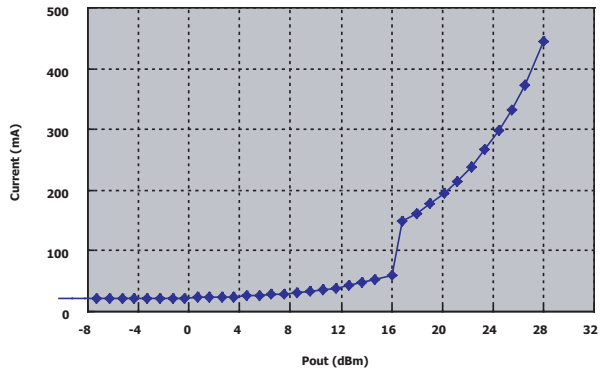
**Table 4-1. Electrical Characteristics for CDMA Mode (Vcc=3.4V, Vref=2.85V, T = 25°C)**

| Characteristics                  |                 | Symbol    | Condition           | Min. | Typ. | Max.  | Unit   |
|----------------------------------|-----------------|-----------|---------------------|------|------|-------|--------|
| Gain                             |                 | Gain_hi   | Pout=28.0 dBm       | 26   | 28   |       | dB     |
|                                  |                 | Gain_low  | Pout=16.0 dBm       | 17   | 20   |       | dB     |
| Power Added Efficiency           |                 | PAE_hi    | Pout=28.0 dBm       | 35   | 41   |       | %      |
|                                  |                 | PAE_low   | Pout=16.0 dBm       | 14   | 18   |       | %      |
| Total Supply Current             |                 | Icc_hi    | Pout=28.0 dBm       |      | 455  |       | mA     |
|                                  |                 | Icc_low   | Pout=16.0 dBm       |      | 65   |       | mA     |
| Quiescent Current                |                 | Iq_hi     | High Power Mode     |      | 100  | 130   | mA     |
|                                  |                 | Iq_low    | Low Power Mode      |      | 22   | 35    | mA     |
| Reference Current                |                 | Iref_hi   | Pout=28.0 dBm       |      | 4    | 10    | mA     |
| Control Current                  |                 | Icont     | Pout=16.0 dBm       |      | 0.5  | 1     | mA     |
| Total Current in Power-down mode |                 | Ipd       | Vref=0V             |      | 0.5  | 5     | µA     |
| ACPR in High power mode          | 0.9 MHz offset  | ACPR1_hi  | Pout=28.0 dBm       |      | -50  | -45   | dBc    |
|                                  | 1.98 MHz offset | ACPR2_hi  | Pout=28.0 dBm       |      | -62  | -57   | dBc    |
| ACPR in Low power mode           | 0.9 MHz offset  | ACPR1_low | Pout=16.0 dBm       |      | -58  | -45   | dBc    |
|                                  | 1.98 MHz offset | ACPR2_low | Pout=16.0 dBm       |      | -64  | -57   | dBc    |
| Harmonic Suppression             | Second          | 2f0       | Pout=28.0 dBm       |      | -33  | -30   | dBc    |
|                                  | Third           | 3f0       | Pout=28.0 dBm       |      | -55  | -40   | dBc    |
| Input VSWR                       |                 | VSWR      |                     |      | 2:1  | 2.5:1 | VSWR   |
| Stability (Spurious Output)      |                 | S         | VSWR 8:1, All phase |      |      | -60   | dBc    |
| Noise Figure                     |                 | NF        |                     |      | 6.8  | 10    | dB     |
| Noise Power in RX Band           |                 | RxBN      | Pout≤28.0 dBm       |      | -138 | -135  | dBm/Hz |
| Ruggedness                       |                 | Ru        | Pin<4.0 dBm         |      |      | 10:1  | VSWR   |
| Switching Time High              | DC              | TswhighDC |                     |      | 1.5  | 5     | µs     |
|                                  | RF              | TswhighRF |                     |      | 35   | 60    | µs     |
| Switching Time Low               | DC              | TswlowDC  |                     |      | 1.5  | 5     | µs     |
|                                  | RF              | TswlowRF  |                     |      | 35   | 60    | µs     |
| Turn On Time                     | DC              | TonDC     |                     |      | 5    | 15    | µs     |
|                                  | RF              | TonRF     |                     |      | 45   | 80    | µs     |
| Turn Off Time                    | DC              | ToffDC    |                     |      | 5    | 15    | µs     |
|                                  | RF              | ToffRF    |                     |      | 45   | 80    | µs     |

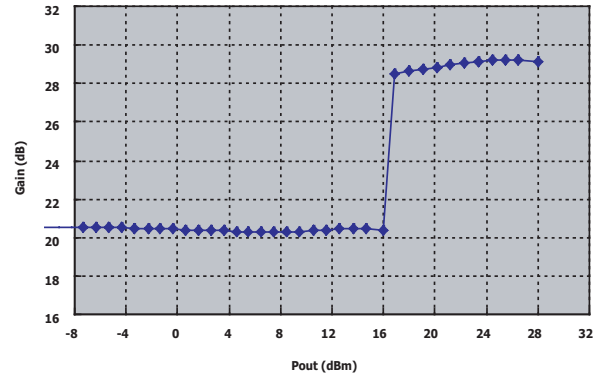
**Table 4-2. Electrical Characteristics for AMPS Mode (Vcc=3.4V, Vref=2.85V, T=25°C)**

| Characteristics             |        | Symbol | Condition           | Min. | Typ. | Max.  | Unit   |
|-----------------------------|--------|--------|---------------------|------|------|-------|--------|
| Gain                        |        | Ga     | Pout=31 dBm         | 25   | 27.5 |       | dB     |
| Power Added Efficiency      |        | PAEa   | Pout=31 dBm         | 45   | 55   |       | %      |
| Total Supply Current        |        | Icca   | Pout=31 dBm         |      | 670  |       | mA     |
| Quiescent Current           |        | Iqa    | High Power Mode     |      | 100  | 130   | mA     |
| Reference Current           |        | Irefa  | Pout=31 dBm         |      | 5.5  | 10    | mA     |
| Harmonic Suppression        | Second | 2fo    | Pout=31.0 dBm       |      | -33  | -30   | dBc    |
|                             | Third  | 3fo    | Pout=31.0 dBm       |      | -50  | -30   | dBc    |
| Input VSWR                  |        | VSWR   |                     |      | 2:1  | 2.5:1 | VSWR   |
| Stability (Spurious Output) |        | S      | VSWR 8:1, All phase |      |      | -60   | dBc    |
| Noise Figure                |        | NF     |                     |      | 6.8  | 10    | dB     |
| Noise Power in RX Band      |        | RxBN   | Pout=31 dBm         |      | -138 | -135  | dBm/Hz |
| Ruggedness                  |        | Ru     | Pin<4 dBm           |      |      | 10:1  | VSWR   |

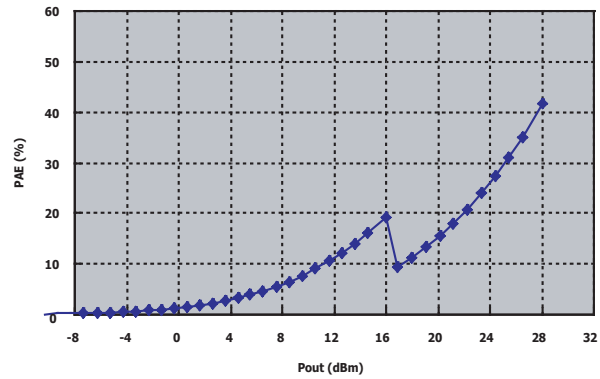
**Characterization Data - CDMA** ( $V_{cc}=3.4V$ ,  $V_{ref}=2.85V$ ,  $T=25^{\circ}C$ ,  $F_o=837MHz$ )



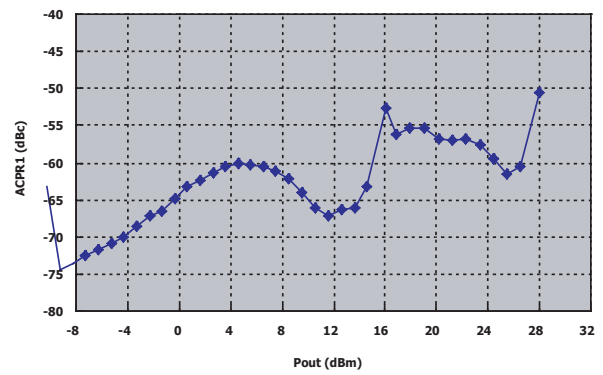
**Figure 1. Total Current vs. Output Power.**



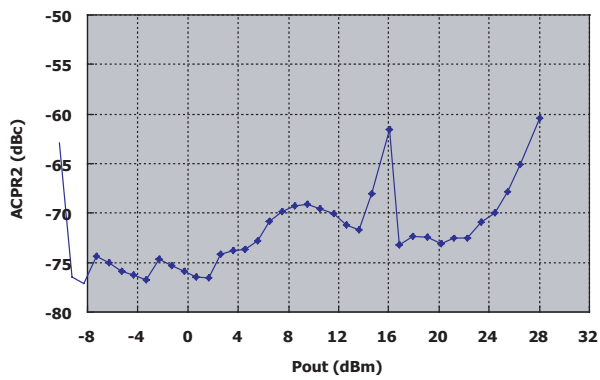
**Figure 2. Gain vs. Output Power.**



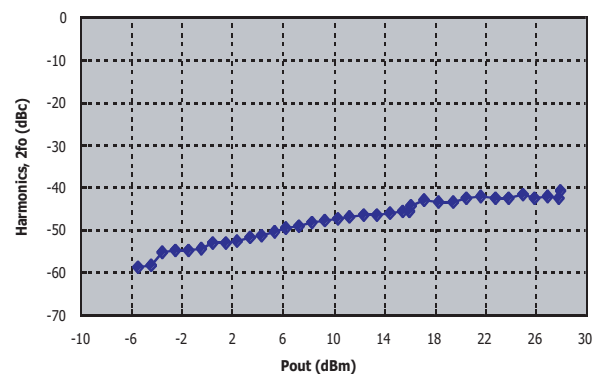
**Figure 3. Power Added Efficiency vs. Output Power.**



**Figure 4. Adjacent Channel Power 1 vs. Output Power.**

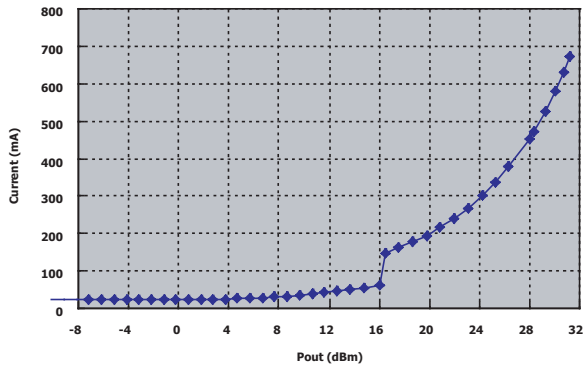


**Figure 5. Adjacent Channel Power 2 vs. Output Power.**

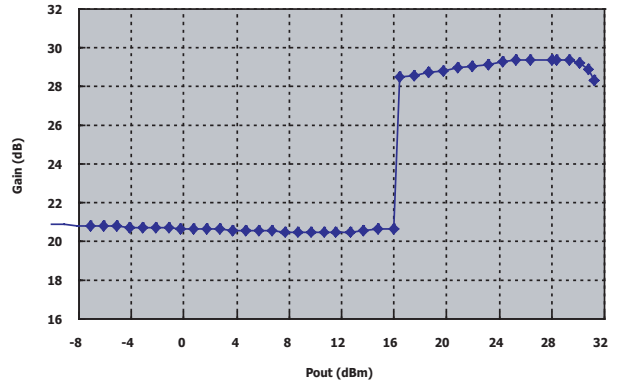


**Figure 6. Harmonic Suppression vs. Output Power.**

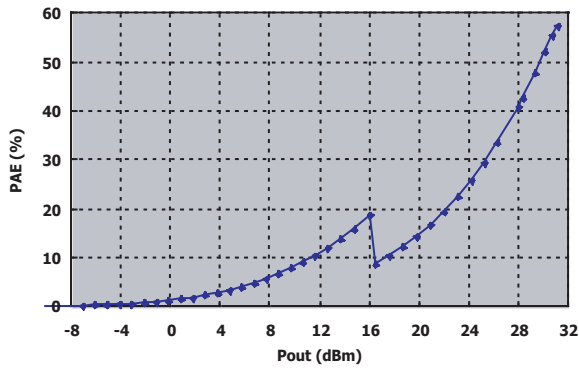
**Characterization Data - AMPS** ( $V_{cc}=3.4V$ ,  $V_{ref}=2.85V$ ,  $T=25^{\circ}C$ ,  $F_o=837MHz$ )



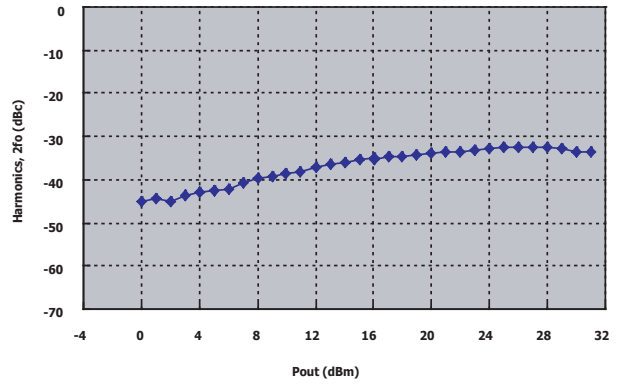
**Figure 7. Total Current vs. Output Power.**



**Figure 8. Gain vs. Output Power.**



**Figure 9. Power Added Efficiency vs. Output Power.**



**Figure 10. Harmonic Suppression vs. Output Power.**

## Evaluation Board Description

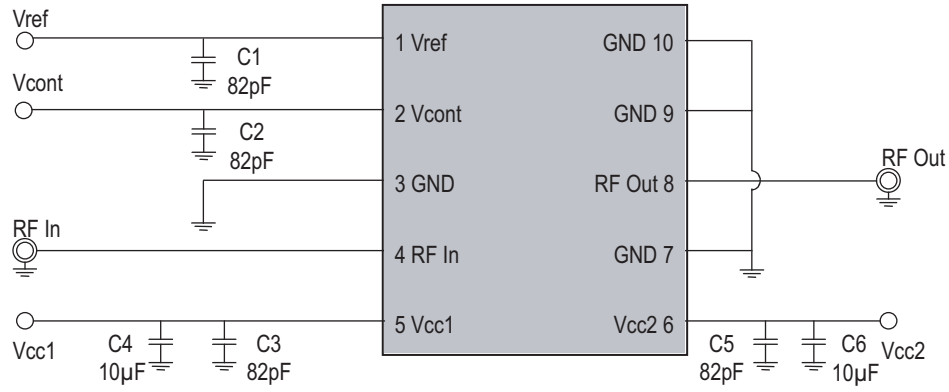


Figure 11. Evaluation Board Schematic.

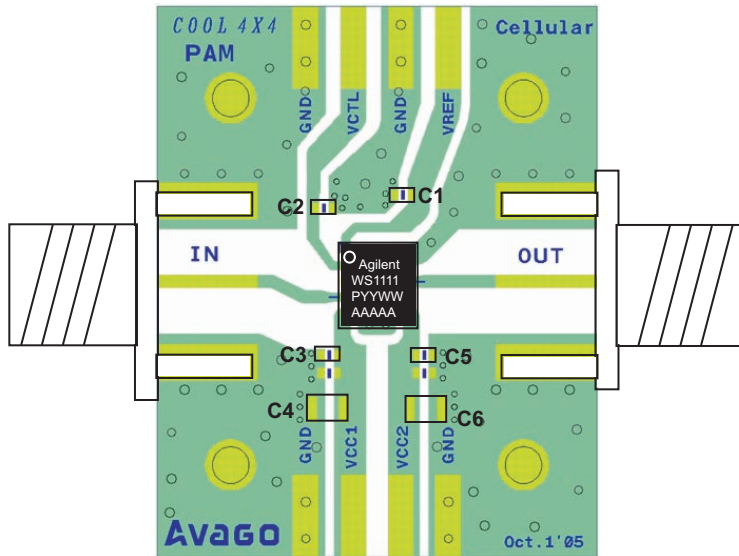


Figure 12. Evaluation Board Assembly Diagram.

# Package Dimensions and Pin Descriptions

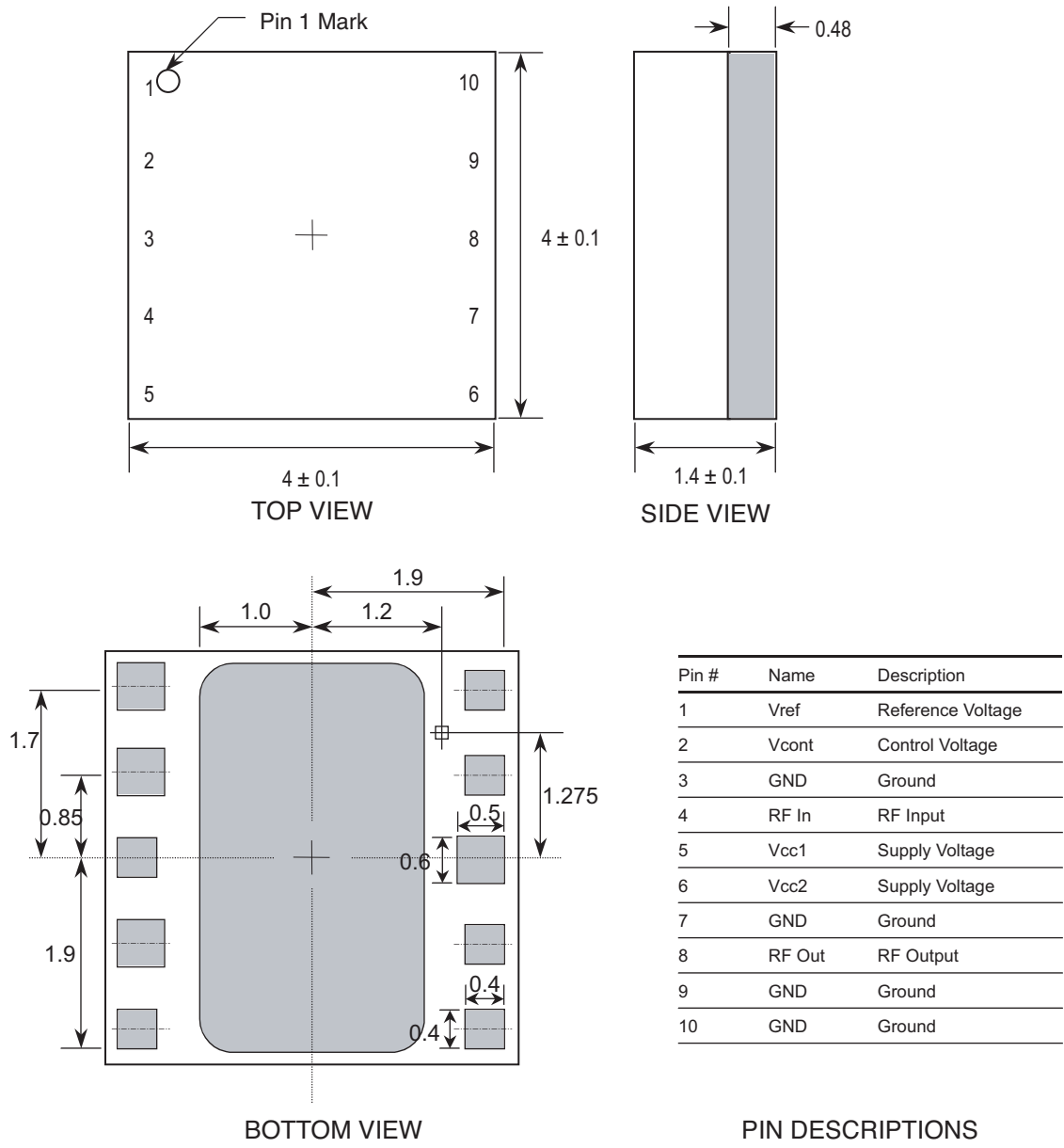
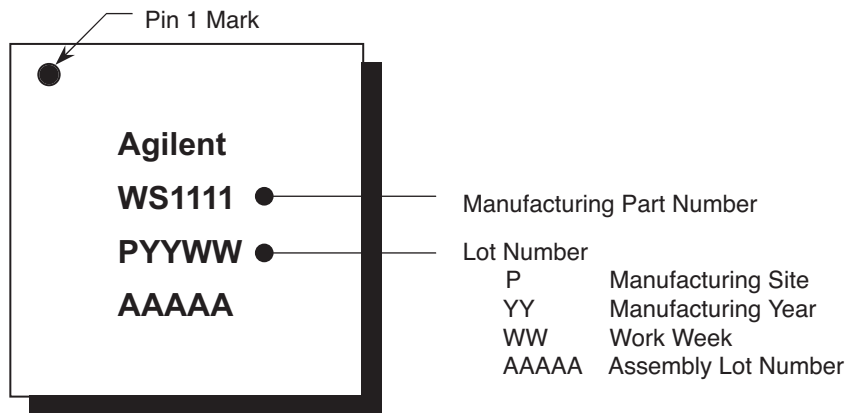


Figure 13. Package Dimensional Drawing and Pin Descriptions (all dimensions are in millimeters).

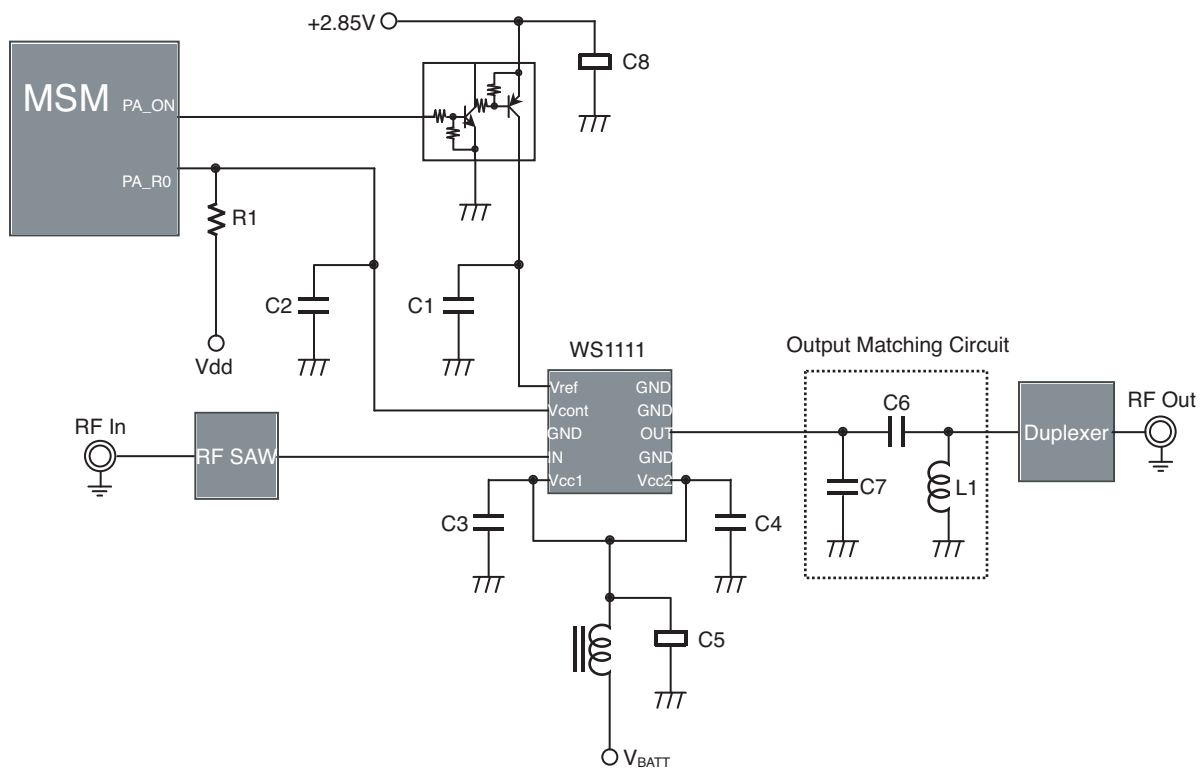


**Package Dimensions and Pin Descriptions, continued**



**Figure 14. Marking Specifications.**

## Peripheral Circuit in Handset



### Notes:

- Recommended voltage for Vref is 2.85V
- Place C1 near to Vref pin.
- Place C3 and C4 close to pin 5 (Vcc1) and pin 6 (Vcc2). These capacitors can affect the RF performance
- Use 50Ω transmission line between PAM and Duplexer and make it as short as possible to reduce conduction loss
- $\pi$ -type circuit topology is good to use for matching circuit between PA and Duplexer.
- Pull-up resistor (R1) should be used to limit current drain

**Figure 15. Peripheral Circuit.**

## Calibration

Calibration procedure is shown in Figure 16. Two calibration tables, high mode and low mode respectively, are required for CoolPAM, which is due to gain difference in each mode.

For continuous output power at the mode change points, the input power should be adjusted according to gain step during the mode change.

## Offset Value

**(difference between rising point and falling point)**

Offset value, which is the difference between the rising point (output power where PA mode changes from

low mode to high mode) and falling point (output power where PA mode changes from high mode to low mode), should be adopted to prevent system oscillation. 3 to 5 dB is recommended for Hysteresis.

## Average Current and Talk Time

Probability Distribution Function implies that what is important for longer talk time is the efficiency of low or medium power range rather than the efficiency at full power. WS1111 idle current is 22 mA and operating current at 16 dBm is 65 mA at nominal condition. These features give extended talk by no less than 30 minutes compared to conventional PAs.

$$\text{Average current} = \int (\text{PDF} \times \text{Current}) dp$$

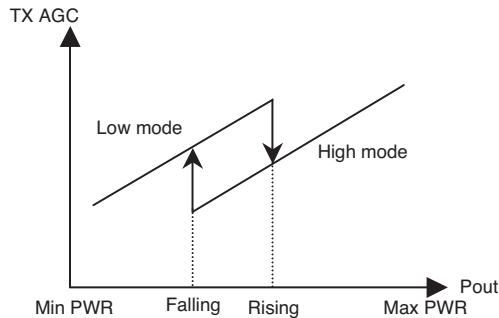


Figure 16. Calibration procedure.

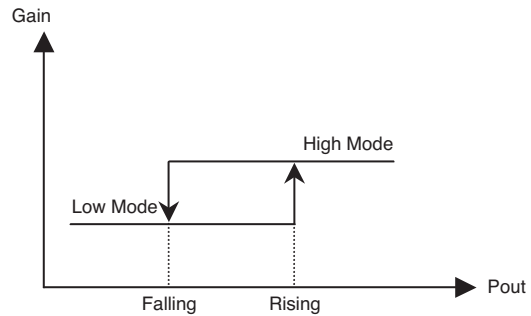


Figure 17. Setting of offset between rising and falling power.

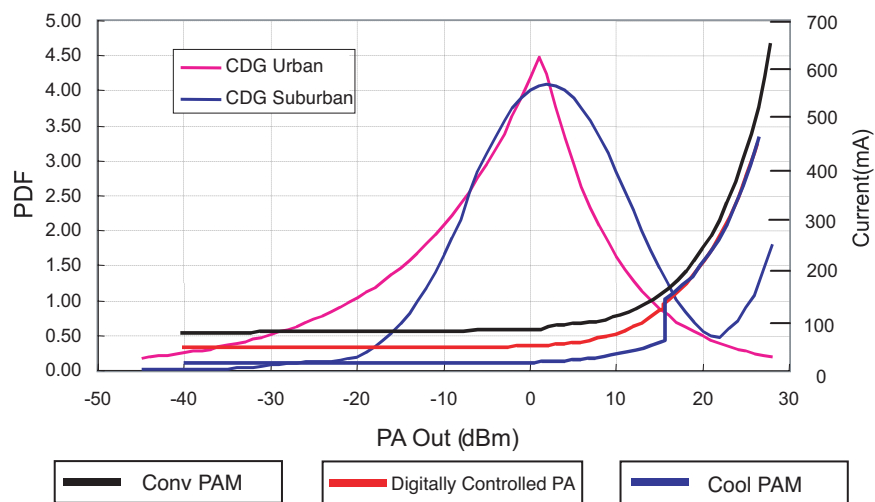


Figure 18. CDMA Power Distribution Function.

### PCB Design Guidelines

The recommended WS1111 PCB Land pattern is shown in Figure 19 and Figure 20. The substrate is coated with solder mask between the I/O and conductive paddle to protect the gold pads from short circuit that is caused by solder bleeding/bridging.

### Stencil Design Guidelines

A properly designed solder screen or stencil is required to ensure optimum amount of solder paste is deposited onto the PCB pads.

The recommended stencil layout is shown in Figure 21. Reducing the stencil opening can potentially generate more voids. On the other hand, stencil openings larger than 100% will lead to excessive solder paste smear or bridging across the I/O pads or conductive paddle to adjacent I/O pads. Considering the fact that solder paste thickness will directly affect the quality of the solder joint, a good choice is to use laser cut stencil composed of 0.100 mm (4mils) or 0.127 mm (5mils) thick stainless steel which is capable of producing the required fine stencil outline.

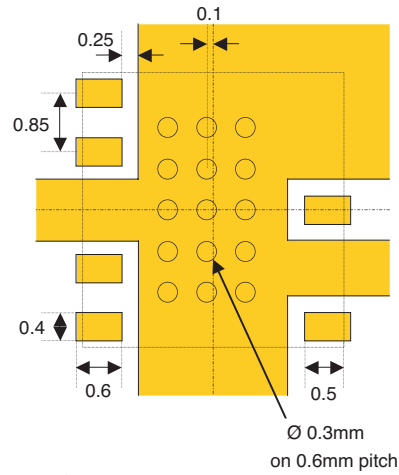


Figure 19. Metallization.

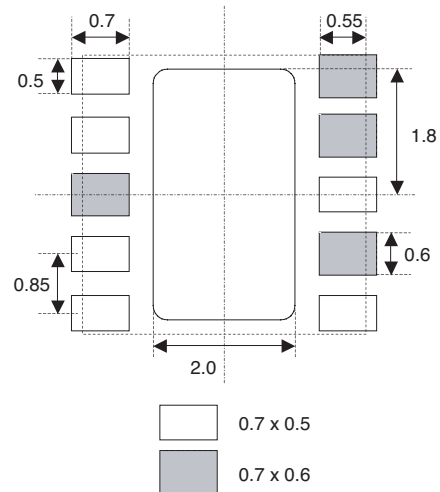


Figure 20. Solder Mask Opening.

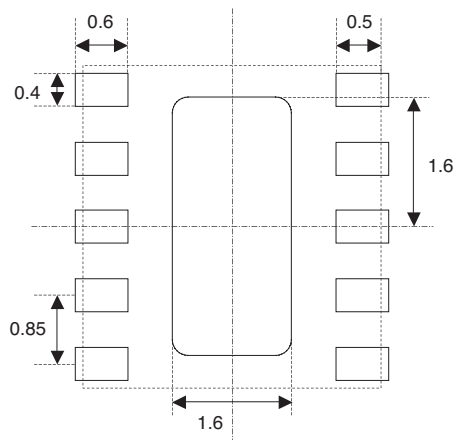
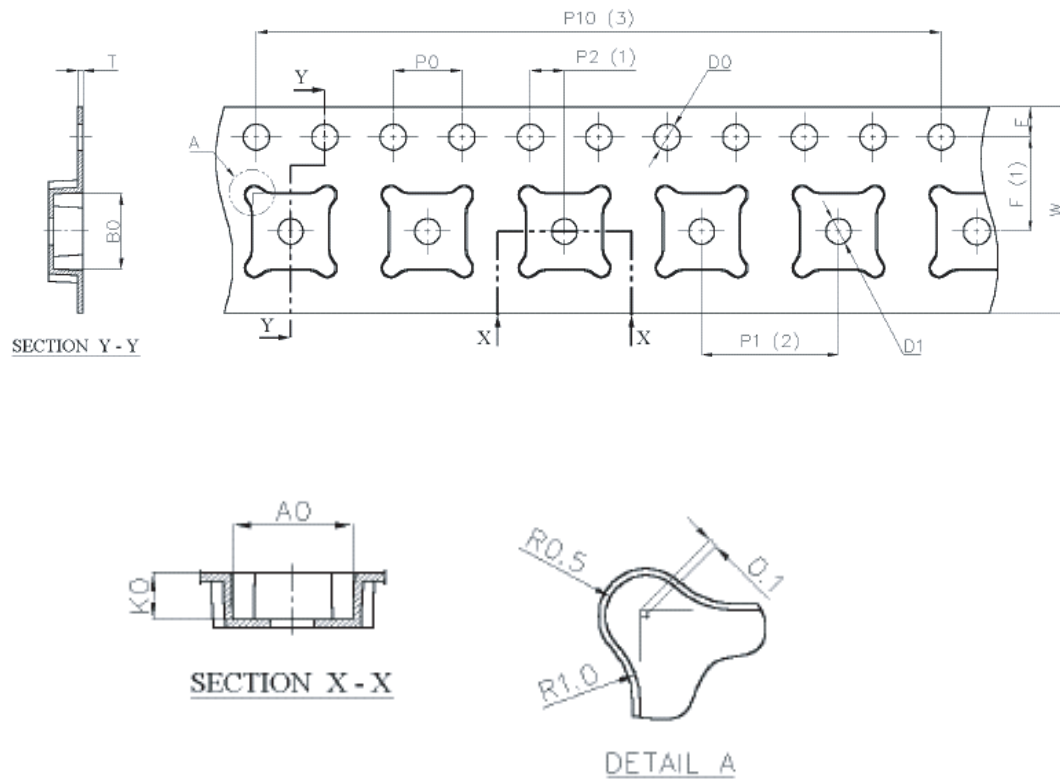


Figure 21. Solder Paste Stencil Aperture.

## Tape and Reel Information



### Dimension List

| Annote | Millimeter | Annote | Millimeter |
|--------|------------|--------|------------|
| A0     | 4.40±0.10  | P2     | 2.00±0.05  |
| B0     | 4.40±0.10  | P10    | 40.00±0.20 |
| K0     | 1.70±0.10  | E      | 1.75±0.10  |
| D0     | 1.55±0.05  | F      | 5.50±0.05  |
| D1     | 1.60±0.10  | W      | 12.00±0.30 |
| P0     | 4.00±0.10  | T      | 0.30±0.05  |
| P1     | 8.00±0.10  |        |            |

Figure 22. Tape and Reel Format – 4 mm x 4 mm.

# Tape And Reel Information, continued

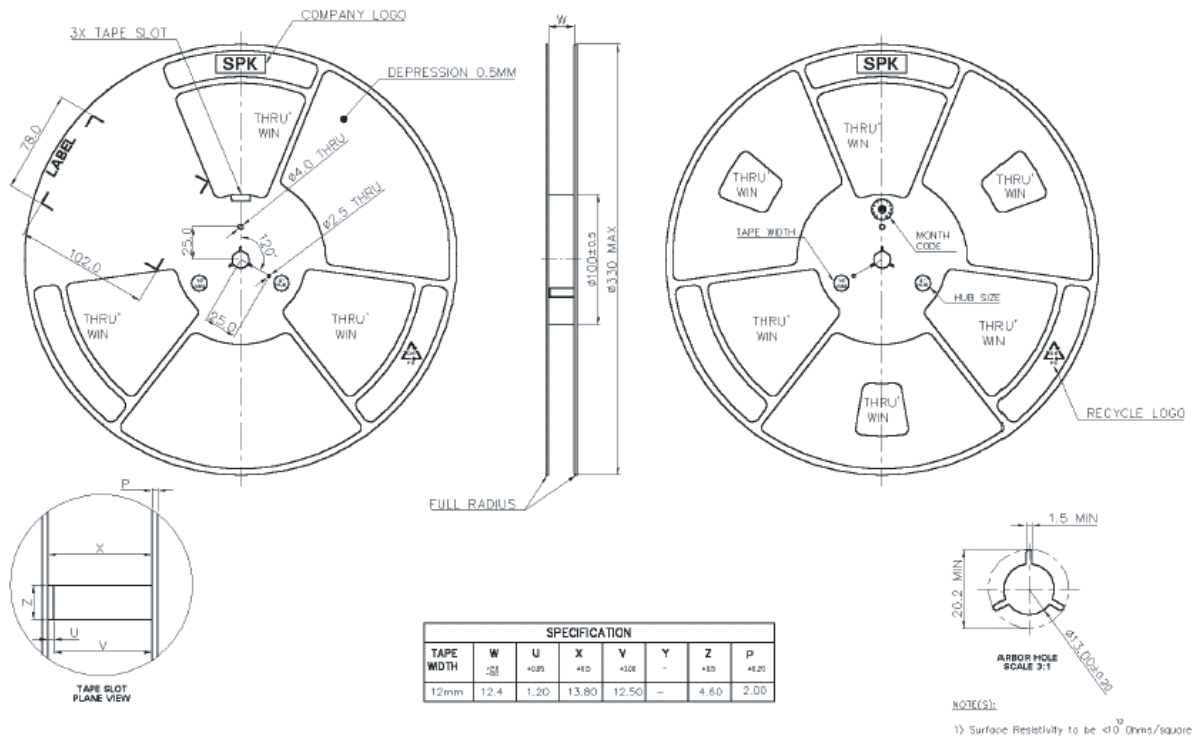


Figure 23. Plastic Reel Format–13"/14" (all dimensions are in millimeters)

## Handling and Storage

### ESD (Electrostatic Discharge)

Electrostatic discharge occurs naturally in the environment. With the increase in voltage potential, the outlet of neutralization or discharge will be sought. If the acquired discharge route is through a semiconductor device, destructive damage will result. ESD countermeasure methods should be developed and used to control potential ESD damage during handling in a factory environment at each manufacturing site.

### MSL (Moisture Sensitivity Level)

Plastic encapsulated surface mount package is sensitive to damage induced by absorbed moisture and temperature. Avago follows JEDEC Standard J-STD 020A. Each component and package type is classified for moisture sensitivity by soaking a known dry

package at various temperatures and relative humidity, and times. After soak, the components are subjected to three consecutive simulated reflows.

The out of bag exposure time maximum limits are determined by the classification test describe above which corresponds to an MSL classification level 6 to 1 according to the JEDEC standard IPC/JEDEC J-STD-020A and J-STD-033.

WS1111 is MSL3. Thus, according to the J-STD-033 p.11 the maximum Manufacturers Exposure Time (MET) for this part is 168 hours. After this time period, the part would need to be removed from the reel, de-taped and then re-bake.

MSL classification reflow temperature for the WS1111 is targeted at 250°C +5/-0°C. Figure 24 and Table 7 show typical SMT profile for maximum temperature of 250°C +5/-0°C.

**Table 5. ESD Classification**

| Pin# | Name   | Description       | HBM     | MM     | Classification |
|------|--------|-------------------|---------|--------|----------------|
| 1    | Vref   | Reference Voltage | ± 2000V | ± 200V | Class 2        |
| 2    | Vcont  | Control Voltage   | ± 2000V | ± 200V | Class 2        |
| 3    | GND    | Ground            | ± 2000V | ± 200V | Class 2        |
| 4    | RF in  | RF Input          | ± 2000V | ± 200V | Class 2        |
| 5    | Vcc1   | Supply Voltage    | ± 2000V | ± 200V | Class 2        |
| 6    | Vcc2   | Supply Voltage    | ± 2000V | ± 200V | Class 2        |
| 7    | GND    | Ground            | ± 2000V | ± 200V | Class 2        |
| 8    | RF Out | RF Output         | ± 2000V | ± 200V | Class 2        |
| 9    | GND    | Ground            | ± 2000V | ± 200V | Class 2        |
| 10   | GND    | Ground            | ± 2000V | ± 200V | Class 2        |

**Note:**

1. Module products should be considered extremely ESD sensitive.

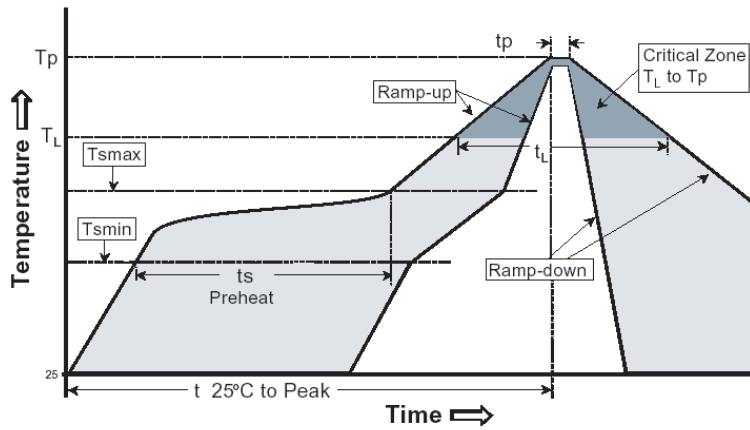
**Table 6. Moisture Classification Level and Floor Life**

| MSL Level | Floor Life (out of bag) at factory ambient ≤30°C/60% RH or as stated                                 |
|-----------|--|
| 1         | Unlimited at ≤30°C/85% RH  |
| 2         | 1 year   |
| 2a        | 4 weeks  |
| <b>3</b>  | <b>168 hours</b>   |
| 4         | 72 hours   |
| 5         | 48 hours   |
| 5a        | 24 hours   |
| 6         | Mandatory bake before use. After bake, must be reflowed within the time limit specified on the label |

**Note:**

1. The MSL Level is marked on the MSL Label on each shipping bag.

**Handling and Storage, continued**



**Figure 24. Typical SMT Reflow Profile for Maximum Temperature = 240 +0/-5°C.**

**Table 7. Typical SMT Reflow Profile for Maximum Temperature = 240+0/-5°C**

| Profile Feature                                      | Sn-Pb Solder | Pb-Free Solder |
|--|--------------|----------------|
| Average ramp-up rate ( $T_L$ to $T_p$ )              | 3°C/sec max  | 3°C/sec max    |
| Preheat  |              |                |
| - Temperature Min ( $T_{smin}$ )                     | 100°C        | 100°C          |
| - Temperature Max ( $T_{smax}$ )                     | 150°C        | 150°C          |
| - Time (min to max) ( $t_s$ )                        | 60–120 sec   | 60–180 sec     |
| $T_{smax}$ to $T_L$                                  |              |                |
| - Ramp-up Rate                                       |              | 3°C/sec max    |
| Time maintained above:                               |              |                |
| - Temperature ( $T_L$ )                              | 183°C        | 217°C          |
| - Time ( $T_L$ )                                     | 60–150 sec   | 60–150 sec     |
| Peak Temperature ( $T_p$ )                           | 225 +0/-5°C  | 240 +0/-5°C    |
| Time within 5°C of actual Peak Temperature ( $t_p$ ) | 10–30 sec    | 10–30 sec      |
| Ramp-down Rate                                       | 6°C/sec max  | 6°C/sec max    |
| Time 25°C to Peak Temperature                        | 6 min max.   | 8 min max.     |



## Handling and Storage, continued

### Storage Conditions

Packages described in this document must be stored in sealed moisture barrier, anti-static bags. Shelf life in a sealed moisture barrier bag is 12 months at <math>40^{\circ}\text{C}</math> and 90% relative humidity (RH) J-STD-033 p.7.

### Out-of-Bag Time Duration

After unpacking the device must be soldered to the PCB within 168 hours as listed in the J-STD-020B p.11 with factory conditions <math>30^{\circ}\text{C}</math> and 60% RH.

### Baking

It is not necessary to re-bake the part if both conditions (storage conditions and out-of-bag condition) have been satisfied. Baking must be done if at least one of the conditions above have not been satisfied. The baking conditions are <math>125^{\circ}\text{C}</math> for 24 hours J-STD-033 p.8.

**CAUTION:** Tape and reel materials typically cannot be baked at the temperature described above. If out-of-bag exposure time is exceeded, parts must be baked for a longer time at low temperatures, or the parts must be re-reeled, de-taped, re-baked and then put back on tape and reel. (See moisture sensitive warning label on each shipping bag for information of baking)

### Board Rework

#### Component Removal, Rework and Remount

If a component is to be removed from the board, it is recommended that localized heating be used and the maximum body temperatures of any surface mount component on the board not exceed <math>200^{\circ}\text{C}</math>. This method will minimize moisture related component damage. If any component temperature exceeds <math>200^{\circ}\text{C}</math>, the board must be baked dry per 4-2 prior to rework and/or component removal. Component temperatures **shall** be measured at the top center of the package body. Any SMD packages that have not exceeded their floor life can be exposed to a maximum body temperature as high as their specified maximum reflow temperature.

### Removal for Failure Analysis

Not following the above requirements may cause moisture/reflow damage that could hinder or completely prevent the determination of the original failure mechanism.

### Baking of Populated Boards

Some SMD packages and board materials are not able to withstand long duration bakes at <math>125^{\circ}\text{C}</math>. Examples of this are some FR-4 materials, which cannot withstand a 24 hr bake at <math>125^{\circ}\text{C}</math>. Batteries and electrolytic capacitors are also temperature sensitive. With component and board temperature restrictions in mind, choose a bake temperature from Table 4-1 in J-STD 033; then determine the appropriate bake duration based on the component to be removed. For additional considerations see IPC-7711 and IPC-7721.

### Derating due to Factory Environmental Conditions

Factory floor life exposures for SMD packages removed from the dry bags will be a function of the ambient environmental conditions. A safe, yet conservative, handling approach is to expose the SMD packages only up to the maximum time limits for each moisture sensitivity level as shown in Table 7. This approach, however, does not work if the factory humidity or temperature are greater than the testing conditions of <math>30^{\circ}\text{C}/60\% \text{RH}</math>. A solution for addressing this problem is to derate the exposure times based on the knowledge of moisture diffusion in the component packaging materials (ref. JESD22-A120). Recommended equivalent total floor life exposures can be estimated for a range of humidities and temperatures based on the nominal plastic thickness for each device. Table 9 lists equivalent derated floor lives for humidities ranging from 20–90% RH for three temperatures, <math>20^{\circ}\text{C}</math>, <math>25^{\circ}\text{C}</math>, and <math>30^{\circ}\text{C}</math>. This table is applicable to SMDs molded with novolac, biphenyl or multifunctional epoxy mold compounds. The following assumptions were used in calculating Table 8:

1. Activation Energy for diffusion = <math>0.35\text{eV}</math> (smallest known value).
2. For  $\leq 60\% \text{RH}$ , use Diffusivity =  $0.121\text{exp}(-0.35\text{eV}/kT)$   $\text{mm}^2/\text{s}$  (this uses smallest known Diffusivity @ <math>30^{\circ}\text{C}</math>).
3. For  $>60\% \text{RH}$ , use Diffusivity =  $1.320\text{exp}(-0.35\text{eV}/kT)$   $\text{mm}^2/\text{s}$  (this uses largest known Diffusivity @ <math>30^{\circ}\text{C}</math>).

## Handling and Storage, continued

**Table 8. Recommended Equivalent Total Floor Life (days) @ 20°C, 25°C & 30°C For ICs with Novolac, Biphenyl and Multifunctional Epoxies (Reflow at same temperature at which the component was classified)**

| Package Type and Body Thickness   | Moisture Sensitivity Level  | Maximum Percent Relative Humidity |     |     |     |     |     |     |     |     |     |      |      |
|---|---|-----------------------------------|-----|-----|-----|-----|-----|-----|-----|-----|-----|------|------|
|   |   | 5%                                | 10% | 20% | 30% | 40% | 50% | 60% | 70% | 80% | 90% |      |      |
| Body Thickness ≥3.1 mm including PQFPs >84 pins, PLCCs (square) All MQFPs or All BGAs ≥1 mm       | Level 2a  | ∞                                 | ∞   | ∞   | 60  | 41  | 33  | 28  | 10  | 7   | 6   | 30°C |      |
|   |   | ∞                                 | ∞   | ∞   | 78  | 53  | 42  | 36  | 14  | 10  | 8   | 25°C |      |
|   |   | ∞                                 | ∞   | ∞   | 103 | 69  | 57  | 47  | 19  | 13  | 10  | 20°C |      |
|   | Level 3   | ∞                                 | ∞   | 10  | 9   | 8   | 7   | 7   | 5   | 4   | 4   | 30°C |      |
|   |   | ∞                                 | ∞   | 13  | 11  | 10  | 9   | 9   | 7   | 6   | 5   | 25°C |      |
|   |   | ∞                                 | ∞   | 17  | 14  | 13  | 12  | 12  | 10  | 8   | 7   | 20°C |      |
|   | Level 4   | ∞                                 | 5   | 4   | 4   | 4   | 3   | 3   | 3   | 2   | 2   | 30°C |      |
|   |   | ∞                                 | 6   | 5   | 5   | 5   | 5   | 4   | 3   | 3   | 3   | 25°C |      |
|   | Level 5   | ∞                                 | 4   | 3   | 3   | 2   | 2   | 2   | 2   | 1   | 1   | 30°C |      |
|   |   | ∞                                 | 5   | 5   | 4   | 4   | 3   | 3   | 2   | 2   | 2   | 25°C |      |
|   | Level 5a  | ∞                                 | 7   | 6   | 5   | 5   | 4   | 4   | 3   | 3   | 3   | 20°C |      |
|   |   | ∞                                 | 2   | 1   | 1   | 1   | 1   | 1   | 1   | 1   | 1   | 30°C |      |
|   |   | ∞                                 | 3   | 2   | 2   | 2   | 2   | 2   | 2   | 1   | 1   | 25°C |      |
|   | Body 2.1 mm ≤ Thickness <3.1 mm including PLCCs (rectangular) 18-32 pins SOICs (wide body) SOICs ≥20 pins, PQFPs ≤80 pins | Level 2a                          | ∞   | ∞   | ∞   | ∞   | 86  | 39  | 28  | 4   | 3   | 2    | 30°C |
|   |   |                                   | ∞   | ∞   | ∞   | ∞   | 148 | 51  | 37  | 6   | 4   | 3    | 25°C |
| ∞   |   |                                   | ∞   | ∞   | ∞   | ∞   | 69  | 49  | 8   | 5   | 4   | 20°C |      |
| Level 3   |   | ∞                                 | ∞   | 19  | 12  | 9   | 8   | 7   | 3   | 2   | 2   | 30°C |      |
|   |   | ∞                                 | ∞   | 25  | 15  | 12  | 10  | 9   | 5   | 3   | 3   | 25°C |      |
|   |   | ∞                                 | ∞   | 32  | 19  | 15  | 13  | 12  | 7   | 5   | 4   | 20°C |      |
| Level 4   |   | ∞                                 | 7   | 5   | 4   | 4   | 3   | 3   | 2   | 2   | 1   | 30°C |      |
|   |   | ∞                                 | 9   | 7   | 5   | 5   | 4   | 4   | 3   | 2   | 2   | 25°C |      |
| Level 5   |   | ∞                                 | 11  | 9   | 7   | 6   | 5   | 4   | 3   | 3   | 3   | 20°C |      |
|   |   | ∞                                 | 4   | 3   | 3   | 2   | 2   | 2   | 1   | 1   | 1   | 30°C |      |
| Level 5a  |   | ∞                                 | 5   | 4   | 3   | 3   | 3   | 3   | 2   | 1   | 1   | 25°C |      |
|   |   | ∞                                 | 6   | 5   | 5   | 4   | 4   | 4   | 3   | 3   | 2   | 20°C |      |
|   |   | ∞                                 | 2   | 1   | 1   | 1   | 1   | 1   | 1   | 0.5 | 0.5 | 30°C |      |
| Body Thickness <2.1 mm including SOICs <18 pins All TQFPs, TSOPs or all BGAs <1 mm body thickness |   | Level 2a                          | ∞   | ∞   | ∞   | ∞   | ∞   | ∞   | 28  | 1   | 1   | 1    | 30°C |
|   |   |                                   | ∞   | ∞   | ∞   | ∞   | ∞   | ∞   | ∞   | ∞   | 2   | 1    | 1    |
|   | ∞   |                                   | ∞   | ∞   | ∞   | ∞   | ∞   | ∞   | ∞   | 2   | 2   | 1    | 20°C |
|   | Level 3   | ∞                                 | ∞   | ∞   | ∞   | ∞   | ∞   | 11  | 7   | 1   | 1   | 1    | 30°C |
|   |   | ∞                                 | ∞   | ∞   | ∞   | ∞   | ∞   | 14  | 10  | 2   | 1   | 1    | 25°C |
|   |   | ∞                                 | ∞   | ∞   | ∞   | ∞   | ∞   | 20  | 13  | 2   | 2   | 1    | 20°C |
|   | Level 4   | ∞                                 | ∞   | ∞   | 9   | 5   | 4   | 3   | 1   | 1   | 1   | 30°C |      |
|   |   | ∞                                 | ∞   | ∞   | 12  | 7   | 5   | 4   | 2   | 1   | 1   | 25°C |      |
|   | Level 5   | ∞                                 | ∞   | ∞   | 17  | 9   | 7   | 6   | 2   | 2   | 1   | 20°C |      |
|   |   | ∞                                 | ∞   | 13  | 5   | 3   | 2   | 2   | 1   | 1   | 1   | 30°C |      |
|   | Level 5a  | ∞                                 | ∞   | 18  | 6   | 4   | 3   | 3   | 2   | 1   | 1   | 25°C |      |
|   |   | ∞                                 | ∞   | 26  | 8   | 6   | 5   | 4   | 2   | 2   | 1   | 20°C |      |
|   |   | ∞                                 | 10  | 3   | 2   | 1   | 1   | 1   | 1   | 1   | 0.5 | 30°C |      |
|   | Level 5a  | ∞                                 | 13  | 5   | 3   | 2   | 2   | 2   | 1   | 1   | 1   | 25°C |      |
|   |   | ∞                                 | 18  | 6   | 4   | 3   | 2   | 2   | 2   | 2   | 1   | 20°C |      |

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